



IRF5803D2TR Information

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Part Number IRF5803D2TR

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 40V 3.4A 8-SOIC **Package** 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF5803D2TR Specifications

Manufacturer Part NumberIRF5803D2TRManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackage8-SOIC (0.154", 3.90mm Width)SeriesFETKY?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250µAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1110pf @ 25VVgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-SOIC (0.154", 3.90mm Width) Series FET KY? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 3.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 37nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1110pF @ 25V Vgs (Max) FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature Supflier Device Package Package / Case B-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	IRF5803D2TR
Package 8-SOIC (0.154", 3.90mm Width) Series FETKY? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 3.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 37nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1110pF @ 25V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Infineon Technologies
Package 8-SOIC (0.154", 3.90mm Width) Series FETKY? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 3.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 37nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1110pF @ 25V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 2W (Ta) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
SeriesFETKY?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250µAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1110pF @ 25VVgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1110pF @ 25VVgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1110pF @ 25VVgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	FETKY?
Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs37nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1110pF @ 25VVgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **EUV FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature Supplier Device Package Package / Case \$-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 37nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	40V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	3.4A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1110pF @ 25V Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	3V @ 250μA
Vgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2W (Ta)Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	37nC @ 10V
FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	1110pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 112 mOhm @ 3.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs112 mOhm @ 3.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	Schottky Diode (Isolated)
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	112 mOhm @ 3.4A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

IRF5803D2TR Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF5803D2TR Payment Methods



















IRF5803D2TR Shipping Methods













If you have any question about IRF5803D2TR, please do not hesitate to contact us!

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